



No.2261A

2SA1562

PNP Epitaxial Planar Silicon Transistor

High- h_{FE} , AF Amp Applications

Applications

- . AF amp, various drivers

Features

- . Adoption of MBIT process
- . High DC current gain
- . Large current capacity
- . Low collector to emitter saturation voltage
- . High V_{EBO}

Absolute Maximum Ratings at $T_a=25^\circ C$

			unit
Collector to Base Voltage	V_{CBO}	-30	V
Collector to Emitter Voltage	V_{CEO}	-25	V
Emitter to Base Voltage	V_{EBO}	-15	V
Collector Current	I_C	-1.2	A
Collector Current(Pulse)	I_{CP}	-2	A
Collector Dissipation	P_C	1	W
		15	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to +150	$^\circ C$

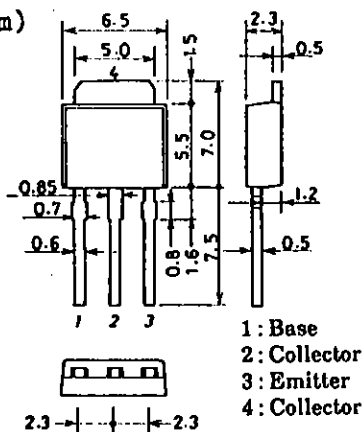
Electrical Characteristics at $T_a=25^\circ C$

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=-20V, I_E=0$			-1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=-10V, I_C=0$			-1	μA
DC Current Gain	$h_{FE}(1)$	$V_{CE}=-5V, I_C=-100mA$	500	800	1200	
	$h_{FE}(2)$	$V_{CE}=-5V, I_C=-10mA$	350			
Gain-Bandwidth Product	f_T	$V_{CE}=-10V, I_C=-50mA$		130		MHz
Output Capacitance	c_{ob}	$V_{CB}=-10V, f=1MHz$		40		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C=-500mA, I_B=-10mA$	-0.1	-0.5		V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C=-500mA, I_B=-10mA$	-0.78	-1.1		V

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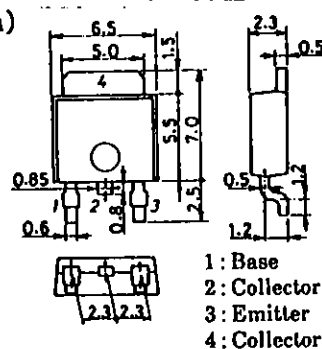
Package Dimensions 2045B

(unit:mm)



Package Dimensions 2044B

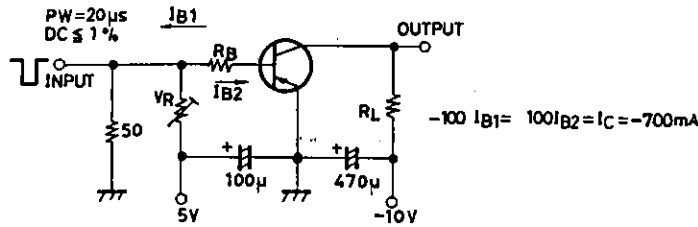
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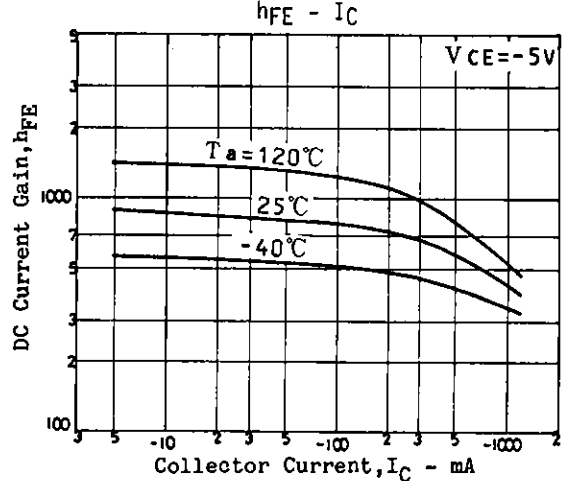
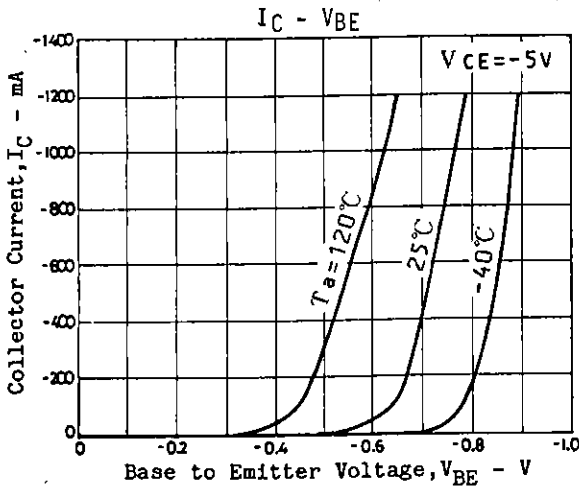
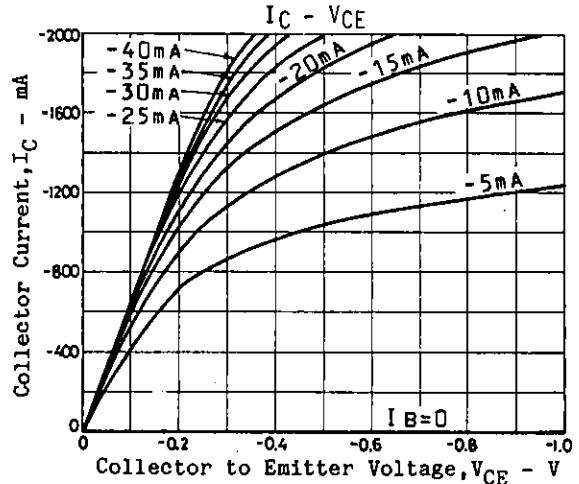
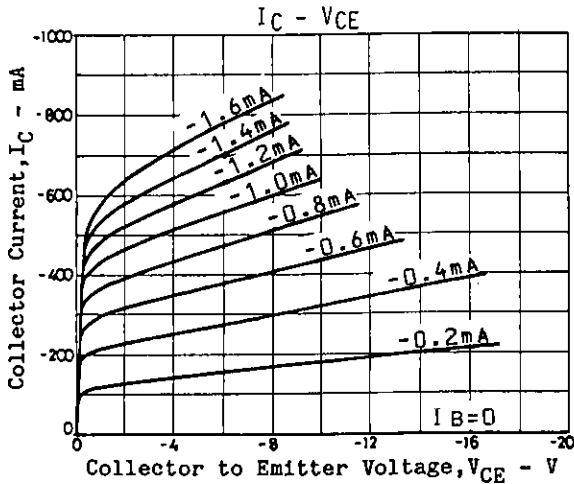
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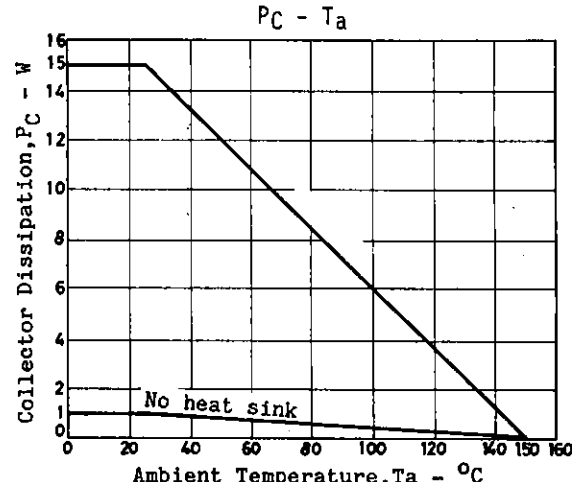
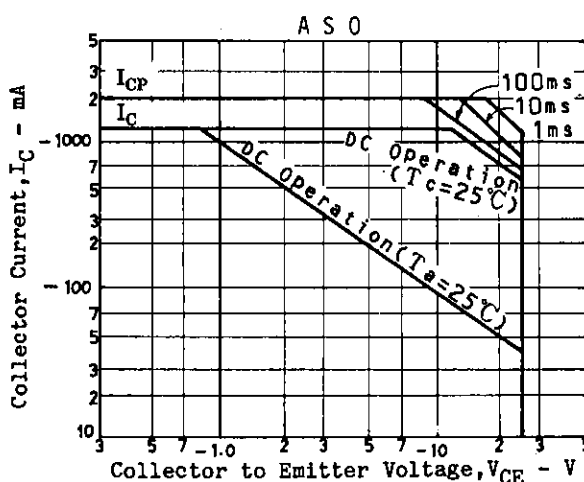
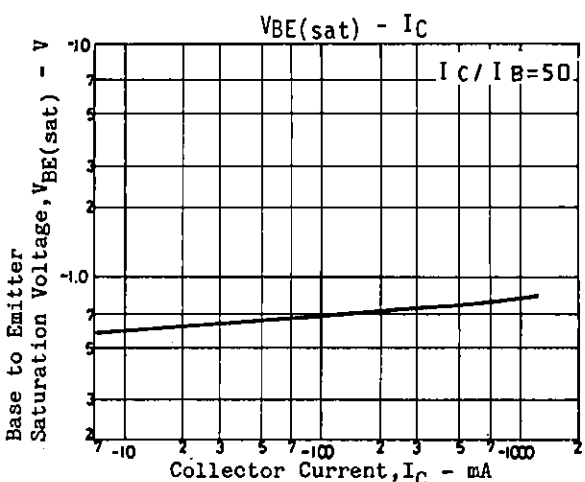
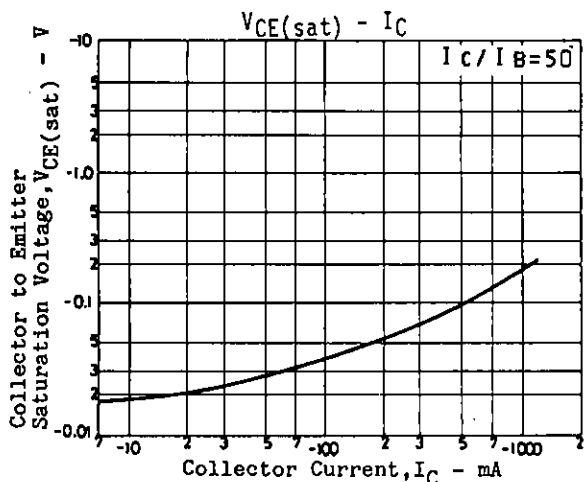
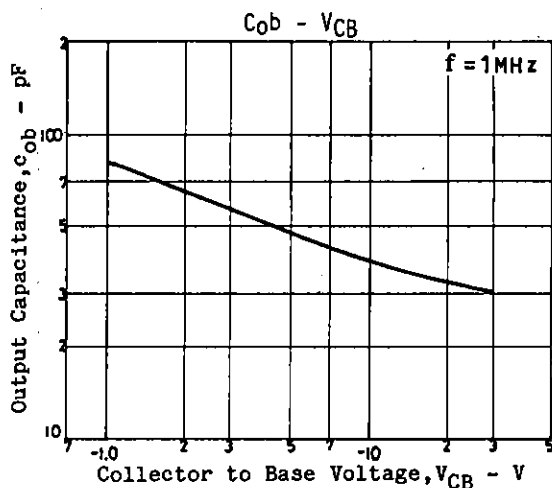
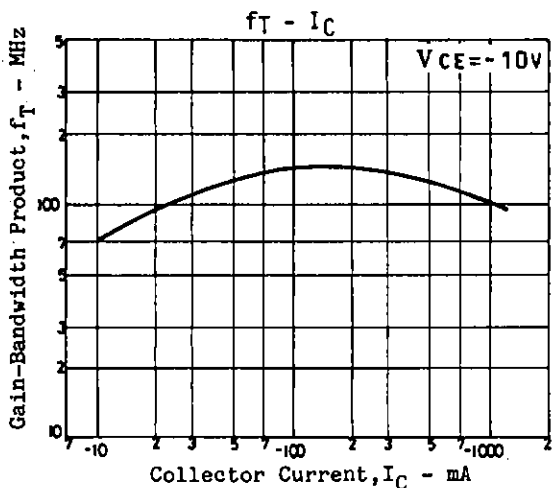
			min	typ	max	unit
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-) 10\mu A, I_E = 0$	-30			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1mA, R_{BE} = \infty$	-25			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -10\mu A, I_C = 0$	-15			V
Turn-ON Time	t_{on}	See specified Test Circuit.	0.31			μs
Storage Time	t_{stg}	"	0.88			μs
Fall Time	t_f	"	0.23			μs

Switching Time Test Circuit



Unit (Resistance : Ω , Capacitance : F)





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